

Contribution submission to the conference SurfaceScience 2021

Transitions from single-layer MoS₂ to bilayer growth: A LEEM study — ●MORITZ EWERT^{1,2,3}, LARS BUSS^{1,2}, FRANCESCA GENUZIO⁴, TEVFIK ONUR MENTES⁴, ANDREA LOCATELLI⁴, JENS FALTA^{2,3}, and JAN INGO FLEGE^{1,2,3} — ¹Applied Physics and Semiconductor Spectroscopy, Brandenburg University of Technology Cottbus-Senftenberg, Germany — ²Institute of Solid State Physics, University of Bremen, Germany — ³MAPEX Center for Materials and Processes, University of Bremen, Germany — ⁴Elettra-Sincrotrone Trieste S.C.p.A., Basovizza, Trieste, Italy

Molybdenum disulfide (MoS₂) is well-known to change from an indirect to a direct semiconductor as a single layer.

We present insights from in-situ low-energy electron microscopy (LEEM) on the extended growth of MoS₂ on the Au(111) surface at elevated temperatures of 720°C. Our continuous growth method leads to the formation of micron-sized single-layer MoS₂ islands. The single-domain character of these islands is confirmed by employing dark-field imaging and micro-diffraction (LEED). This also reveals the distribution of 90:10 of the two expected MoS₂ mirror domains on Au(111). Selected-area angle-resolved photoelectron spectroscopy (ARPES) measurements of these mirror domains underline the three-fold symmetry of the two mirror domains and indicate the presence of MoS₂ bilayer. Using X-ray photoemission electron microscopy (XPEEM) and intensity-voltage LEEM (I(V))-LEEM we identify the bilayer nucleation areas at nearly full surface coverage and propose a model pathway for their formation.

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